



DATA SHEET

SEMICONDUCTOR

HER501 THRU HER508

5.0AMP HIGH EFFICIENT RECTIFIERS
VOLTAGE RANGE: 50 TO 1000 VOLTS



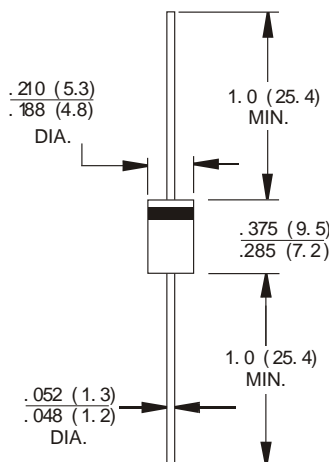
FEATURES

- Low cost
- Diffused junction
- Low Leakage
- Low forward voltage
- High current capability
- Easily cleaned with Freon, Alcohol, Isopropanol and similar solvents
- The plastic material carries U/L recognition 94 V-0

MECHANICAL DATA

- Case: Molded plastic , DO-201AD
- Terminals: Plated axial leads, solderable per MIL-STD-202, Method 208
- Polarity: Color band denotes cathode
- Mounting Position: Any

DO-201AD Unit:inch(mm)



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase. half wave. 60HZ. resistive or inductive load. For capacitive load. derate current by 20%

	SYMBOL	HER501	HER502	HER503	HER504	HER505	HER506	HER507	HER508	UNITS
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	300	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	210	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	300	400	600	800	1000	V
Maximum Average Forward Rectified Current 9.5mm Lead Length. $T_A = 55^\circ C$	$I_{(AV)}$	5.0								A
Peak Forward Surge Current 8.3ms Single Single half-sine-wave superimposed on rated $T_j = 125^\circ C$	I_{FSM}	200								A
Maximum Forward Voltage at 5.0A DC	V_F	1.0		1.3		1.7				V
Maximum Reverse Current $T_A = 25^\circ C$ at Rated DC Blocking Voltage $T_A = 100^\circ C$	I_R	10.0 200.0								μA
Typical Junction Capacitance (Note 1)	C_j	80				50				pF
Maximum reverse recovery time (Note 2)	T_{rr}	50				75				ns
Operating Junction Temperature Range	T_j	- 55 to 150								$^\circ C$
Storage Temperature Range	T_{STG}	- 55 to 150								$^\circ C$

- NOTE:** 1. Measured at 1.0MHZ and applied reverse voltage of 4.0V DC.
2. Thermal resistance junction to ambient.

FIG. 1 -- TYPICAL FORWARD CHARACTERISTIC

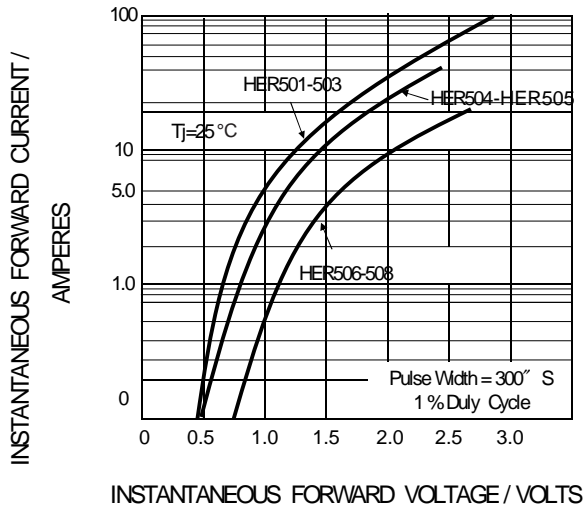


FIG. 2 -- TYPICAL JUNCTION CAPACITANCE

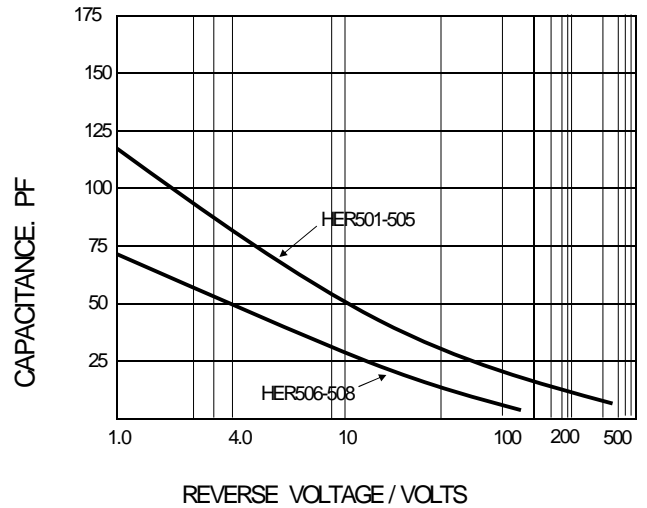


FIG. 3-- FORWARD CURRENT DERATING CURVE

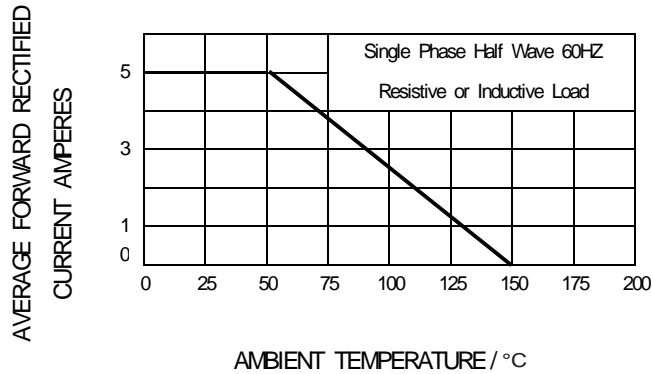


FIG. 4-- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

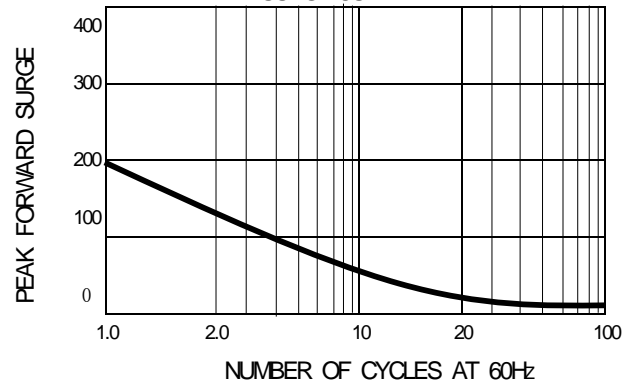
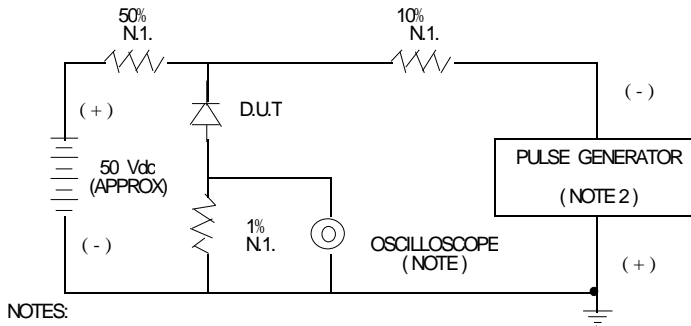
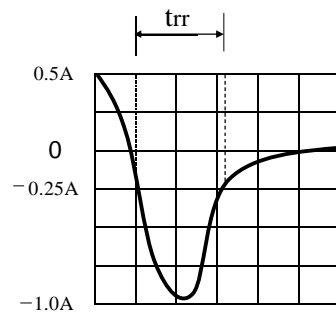


FIG. 5-- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC



- NOTES:
1. RISE TIME = 7n SEC MAX. INPUT IMPEDANCE = 1 MEGOHM 22PF
 2. RISE TIME = 10n SEC MAX. SOURCE IMPEDANCE = 50 OHM



SET TIME BASE FOR 15 ns/cm